

N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY			
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ)
30	0.00375 at V _{GS} = 10 V	34	35.7 nC
	0.0047 at V _{GS} = 4.5 V	30	

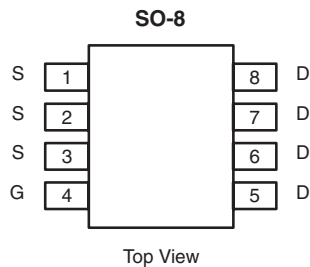
FEATURES

- SkyFET™ Monolithic TrenchFET® Power MOSFET and Schottky Diode
- 100 % R_g and UIS Tested

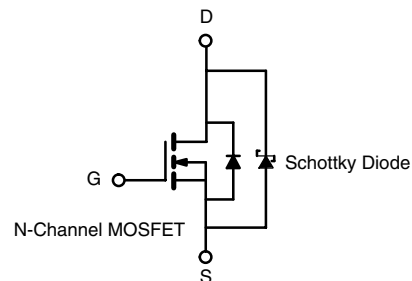
RoHS
COMPLIANT

APPLICATIONS

- Notebook CPU Core
- Buck Converter
- Synchronous Rectifier Switch



Ordering Information: Si4642DY-T1-E3 (Lead (Pb)-free)



ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	34
		T _C = 70 °C	27
		T _A = 25 °C	22.7 ^{b, c}
		T _A = 70 °C	18 ^{b, c}
Pulsed Drain Current	I _{DM}	70	A
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	
		T _A = 25 °C	3.1 ^{b, c}
Single Pulse Avalanche Current	I _{AS}	45	mJ
Single Pulse Avalanche Energy	E _{AS}	101	
Maximum Power Dissipation	P _D	T _C = 25 °C	7.8
		T _C = 70 °C	5
		T _A = 25 °C	3.5 ^{b, c}
		T _A = 70 °C	2.2 ^{b, c}
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typ	Max	Unit
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 sec	R _{thJA}	29	35	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	13	16	

Notes:

a. Based on T_C = 25 °C.

b. Surface Mounted on 1" x 1" FR4 Board.

c. t = 10 sec.

d. Maximum under Steady State conditions is 80 °C/W.

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	30			V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 1\text{ mA}$	1.5		3	
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$		0.05	0.2	mA
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 100\text{ }^\circ\text{C}$		5.5	50	
On -State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	40			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		0.0031	0.00375	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 15\text{ A}$		0.0039	0.0047	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 20\text{ A}$		108		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		5540		pF
Output Capacitance	C_{oss}			790		
Reverse Transfer Capacitance	C_{rss}			346		
Total Gate Charge	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		74	110	nC
				35.7	54	
Gate-Source Charge	Q_{gs}	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		16.8		
Gate-Drain Charge	Q_{gd}			10.7		
Gate Resistance	R_g	$f = 1\text{ MHz}$		1.5	2.3	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 3\text{ }\Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 4.5\text{ V}, R_G = 1\text{ }\Omega$		76	115	ns
Rise Time	t_r			180	270	
Turn-Off Delay Time	$t_{d(off)}$			53	80	
Fall Time	t_f			50	75	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 3\text{ }\Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 10\text{ V}, R_G = 1\text{ }\Omega$		17	26	
Rise Time	t_r			24	36	
Turn-Off Delay Time	$t_{d(off)}$			46	70	
Fall Time	t_f			9	15	
Drain-Source Body Diode and Schottky Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			7	A
Pulse Diode Forward Current ^a	I_{SM}				70	
Body Diode Voltage	V_{SD}	$I_S = 2\text{ A}$		0.44	0.53	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 13\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		36	55	ns
Body Diode Reverse Recovery Charge	Q_{rr}			34	52	nC
Reverse Recovery Fall Time	t_a			19		ns
Reverse Recovery Rise Time	t_b			17		

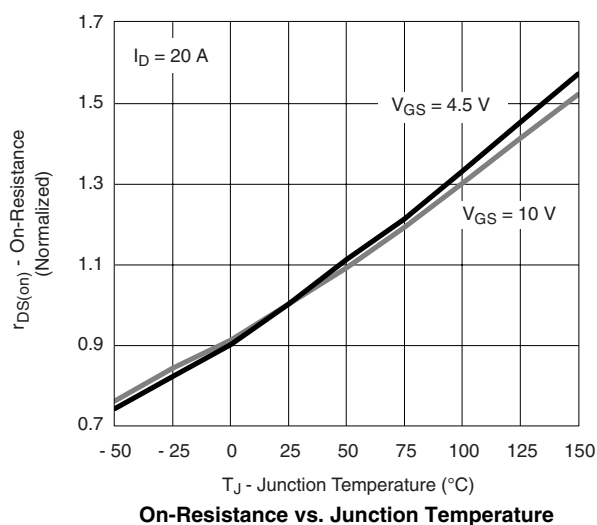
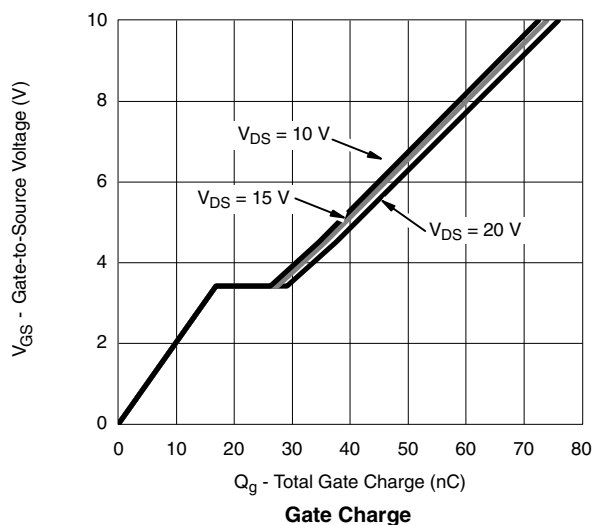
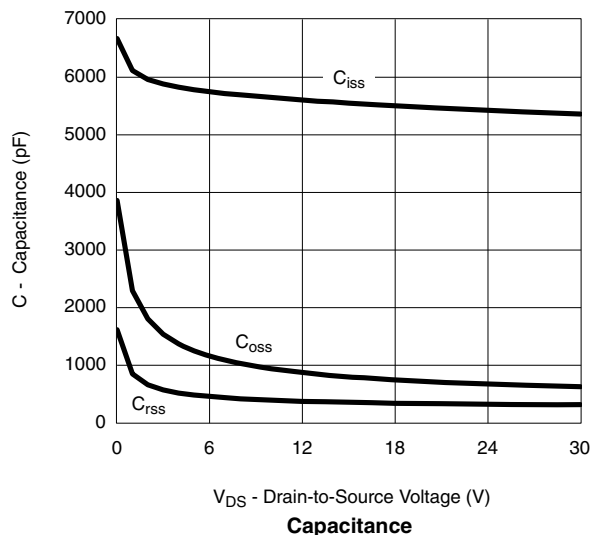
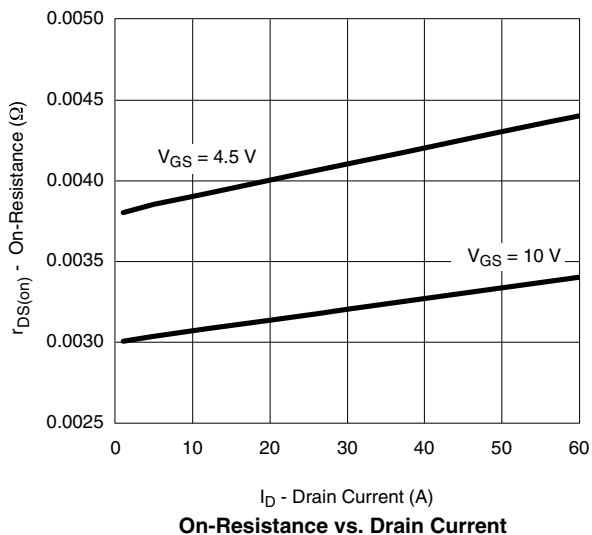
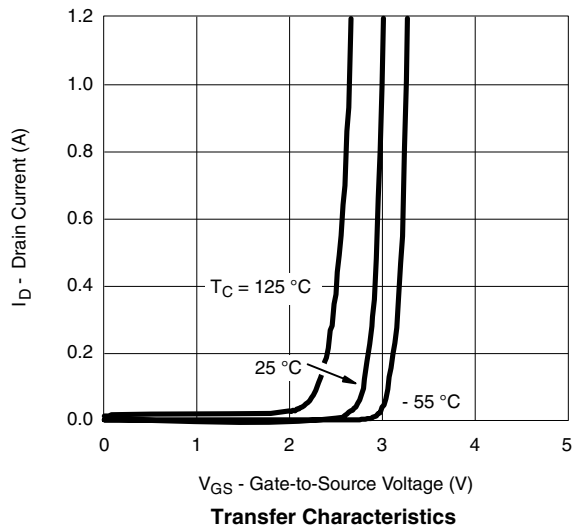
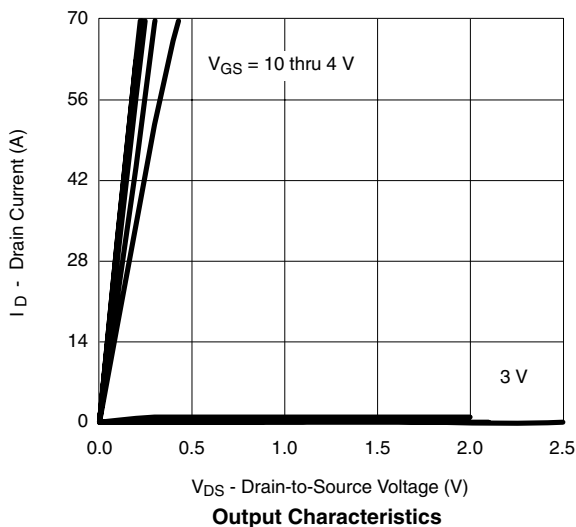
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

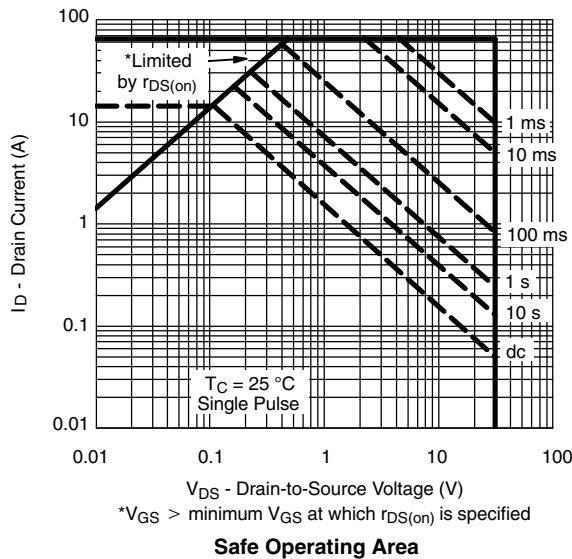
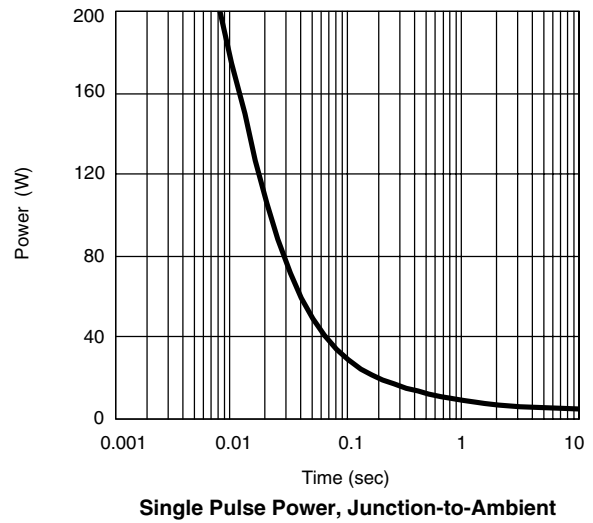
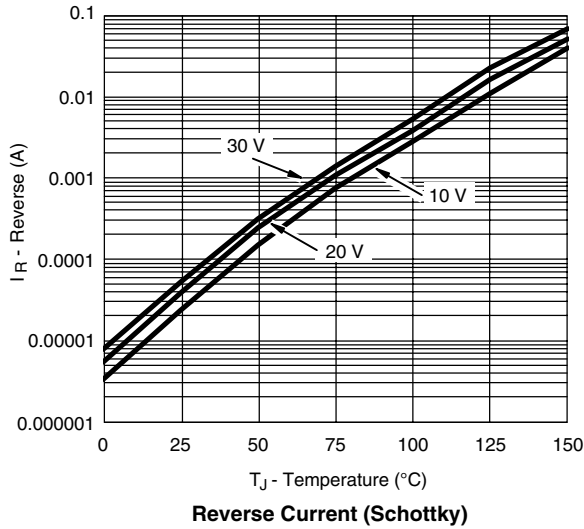
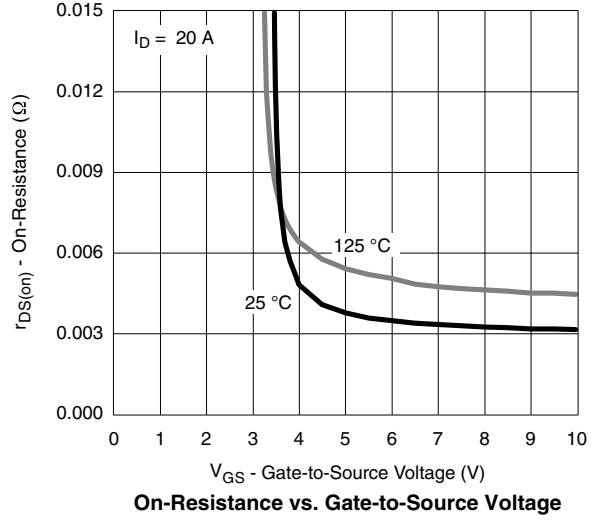
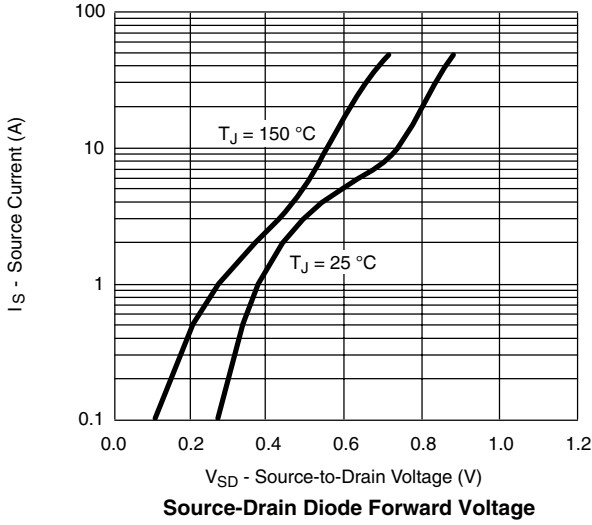


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



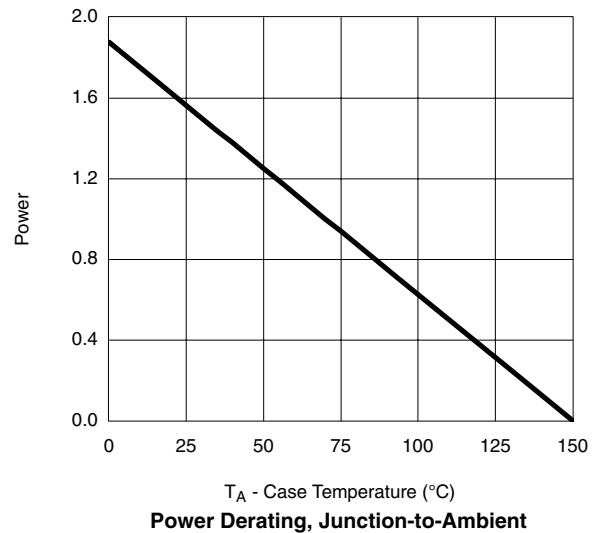
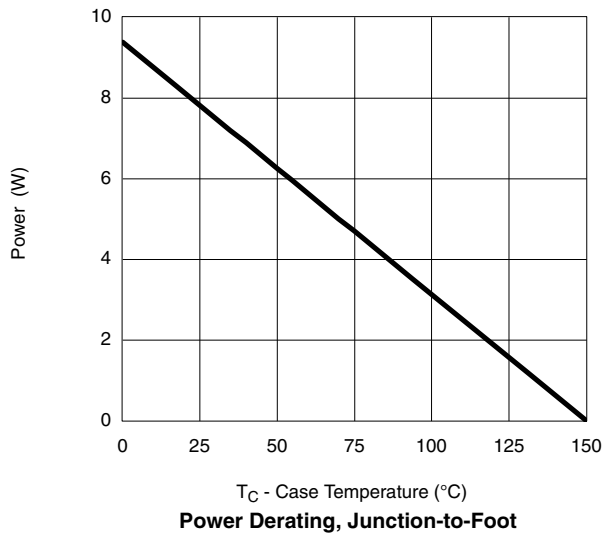
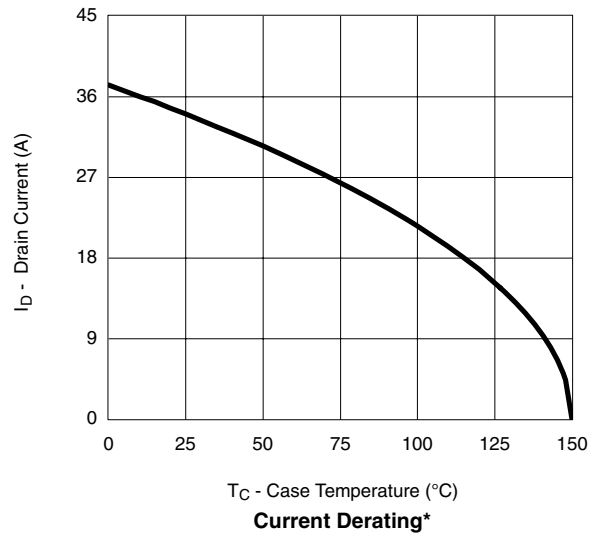


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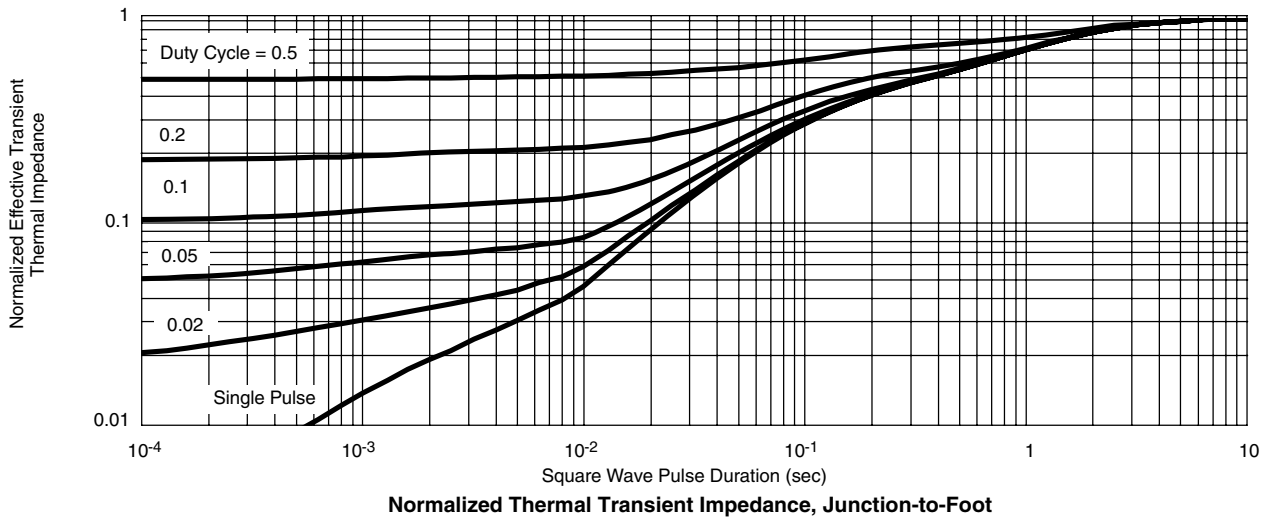
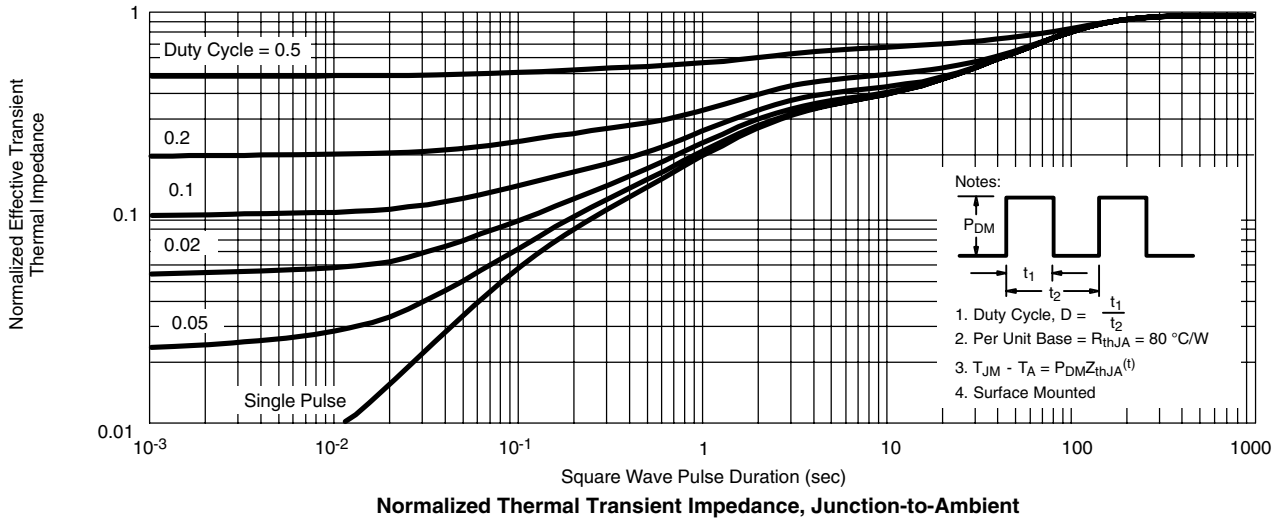
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

Si4642DY



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